AMENDMENTS TO THE CLAIMS

Please amend the Claims as follows:

Claims 1-6 (Canceled)

7. (Currently Amended) A light emitting diode comprising a pellet, a major front surface of which, where an electrode is formed, is made of a GaAsP mixed crystal, characterized in that the major front surface is a rough surface; and characterized in that all side surfaces of the pellet are rough surfaces.

8. (Canceled)

9. (Currently Amended) A light emitting diode according to claim 7, characterized in that the rough ~~surface is~~ surfaces are formed with fine projections having a diameter in a range of from 0.3 μm to 3μm.

10. (Canceled)

11. (Currently Amended) A fabrication process for a light emitting diode having a pellet, a major front surface of which, where an electrode is formed, is made of a GaAsP mixed crystal, characterized in that the pellet is treated with an etching solution of an aqueous solution containing Br_2, nitric acid, hydrofluoric acid and acetic acid or I_2,

nitric acid, hydrofluoric acid, and acetic acid to form fine projections on ~~at least~~ the major front surface and all side surfaces of the pellet.

12. (Canceled)

13. (Previously Presented) A fabrication process for a light emitting diode according to claim 11, characterized in that the etching solution contains 40 to 80 parts of nitric acid, 40 to 300 parts of hydrofluoric acid and 400 to 2000 parts of acetic acid based on 1 part of Br_2 or I_2 in a molar ratio.

14. (Previously Presented) The method of claim 11, wherein the fine projections have a diameter in a range of from 0.3 μm to 3μm.